

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

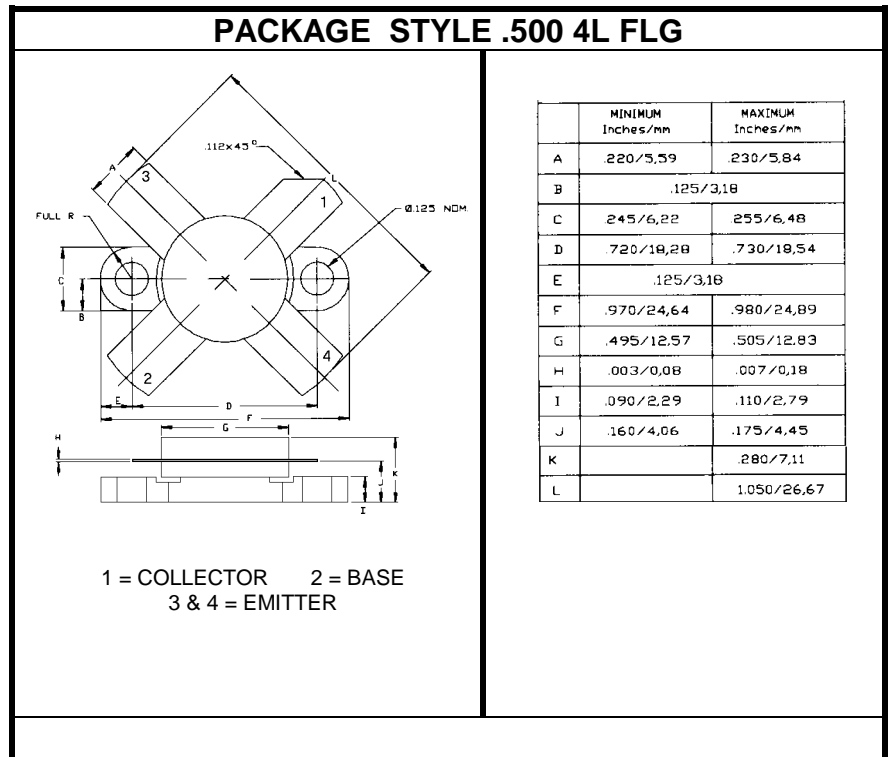
The **ASI BLW77** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

## FEATURES:

- $P_G = 12$  dB min. at 15-30 W/1.6-28 MHz
- Common Emitter
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

$I_C$	12 A
$V_{CB}$	70 V
$V_{CE}$	35 V
$P_{DISS}$	245 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	0.71 °C/W



## CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 100$ mA	35			V
$BV_{CES}$	$I_C = 50$ mA	70			V
$BV_{EBO}$	$I_E = 20$ mA	4.0			V
$I_{CES}$	$V_E = 35$ V			20	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 7.0$ A	15		80	---
$C_c$	$V_{CB} = 28$ V $f = 1.0$ MHz		225		pF
$G_P$	$V_{CE} = 28$ V $I_{C(ZS)} = 0.1$ A $f = 1.6-28$ MHz $P_L = 15-30$ W (PEP)	12			dB
$d_3$				-30	dB
$\eta$		37.5			%